

# NINE project 2010 April update

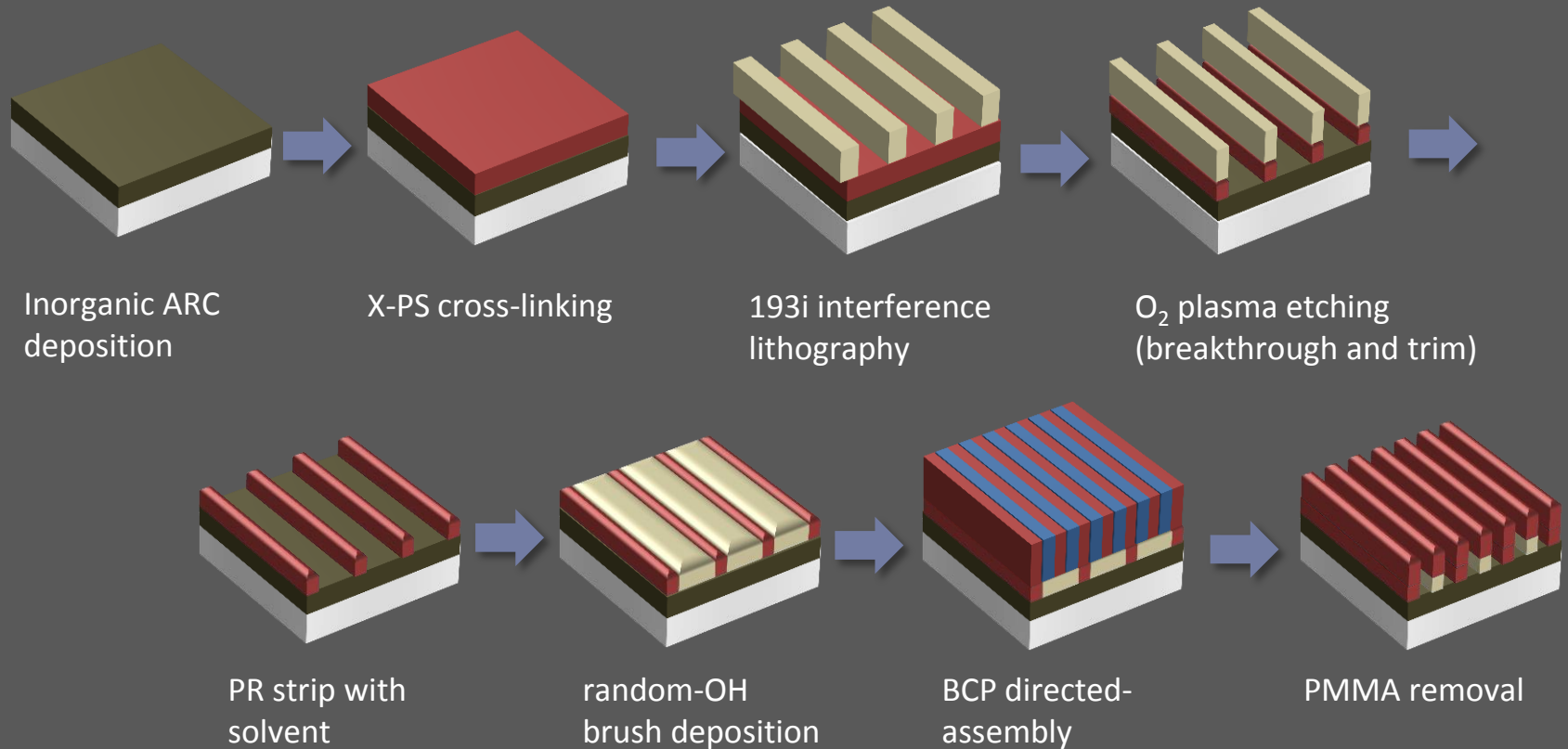
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# Outline

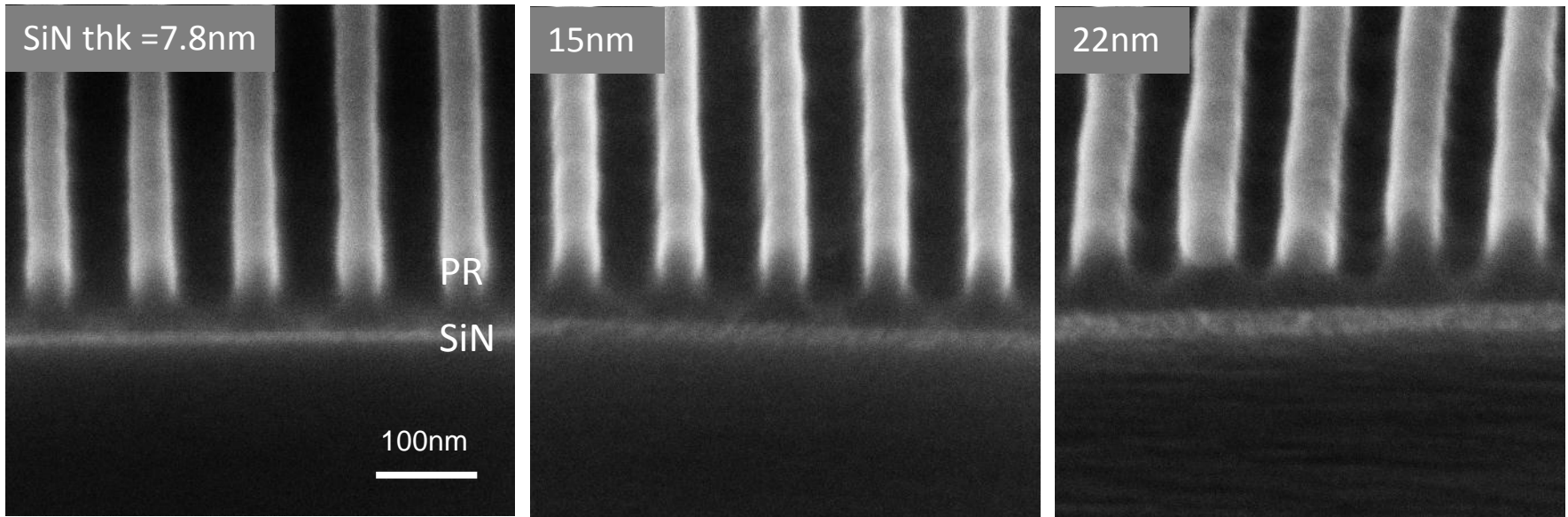
- Process flow
- Optimization of key parameters
  - Line width of guiding patterns (by trim etch)
  - Background chemistry (using different brushes)
- An example of quasi-optimized BCP directed assembly
- Summary and future plan

# Chemically patterned substrate fabricated by 193i-IL

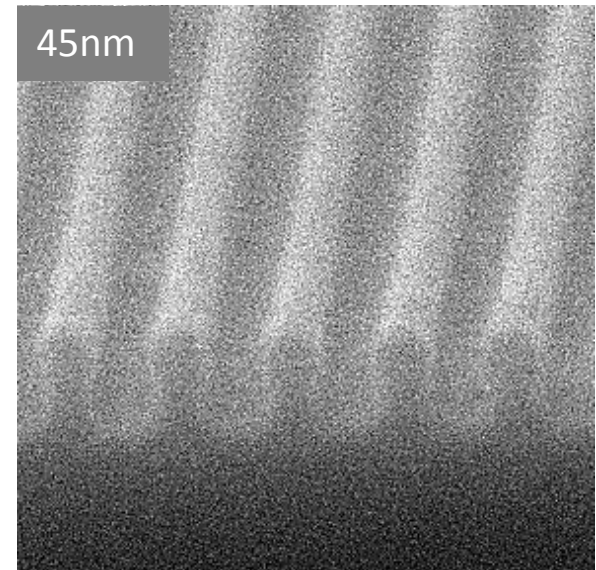
## Process flow



# Thickness effect of the inorganic ARC on PR profile

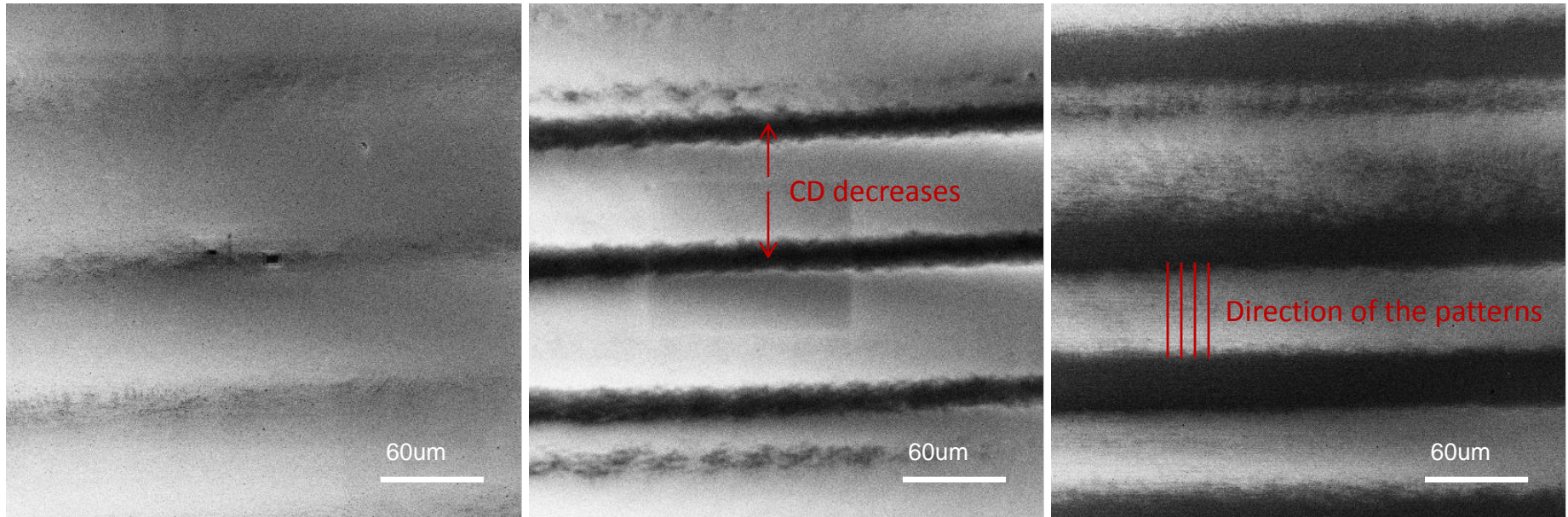


- Samples are made during 09' Dec, before the PM (preventive maintenance) of the 193i-IL tool. (Dose=110 pulses)
- Experiments show that **8~20nm of UW's PECVD nitride is suitable as an ARC.**
- Non-optimized ARC will result in “hot-air balloon” shape of profile.
- Characterization of the optical properties of the nitride film is under-going.

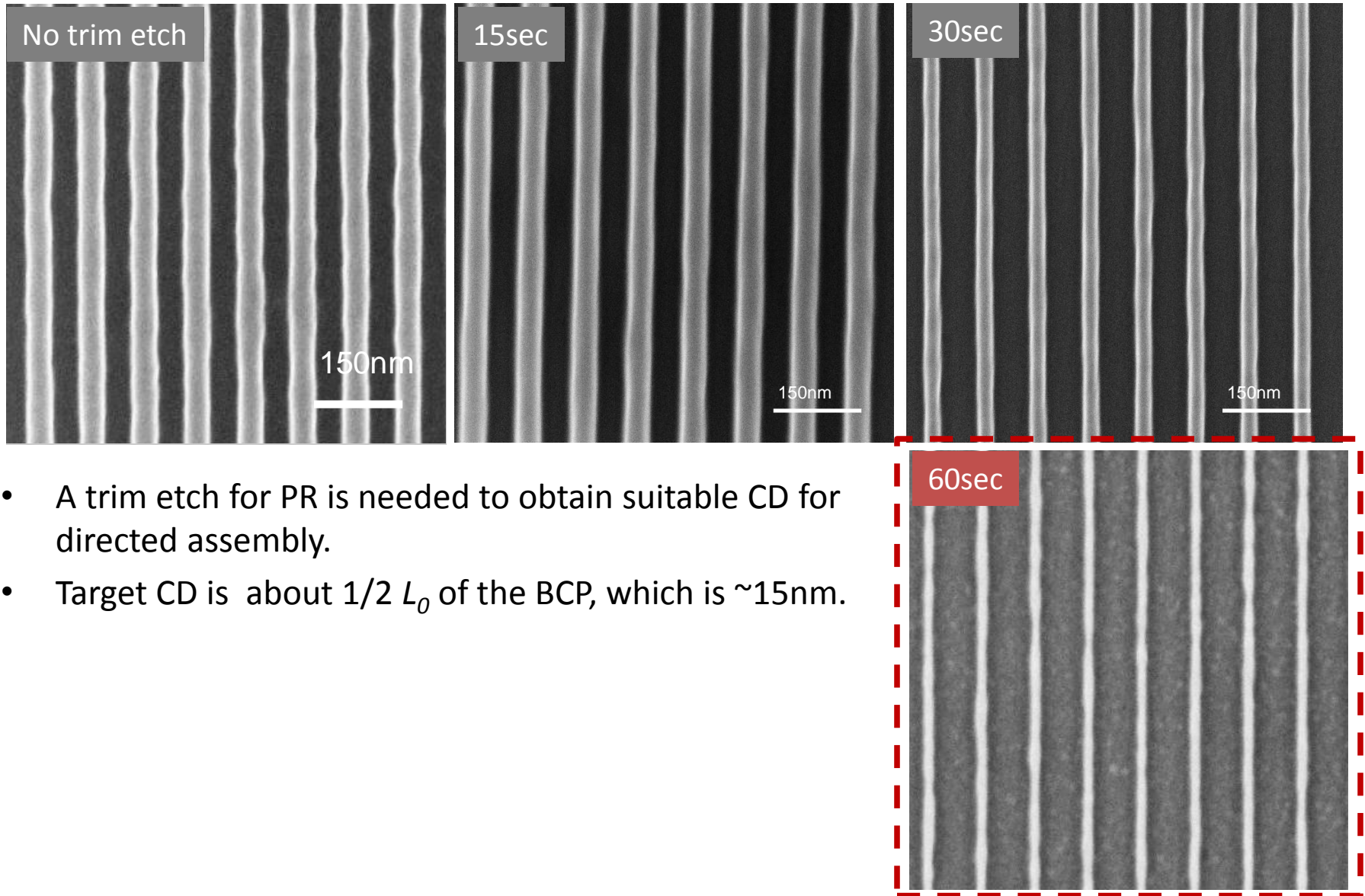


# Spatial uniformity within an exposure field

- Grating pattern over  $\sim 1 \text{ in.}^2$  are obtained. **Segments of parallel lines with  $\sim 50 \mu\text{m}$  in length** can be obtained.
- Nitride 8nm, 110pulses, one exposure field cut into four  $\sim 1 \text{ cm}$ -by- $1 \text{ cm}$  chips. Some spatial differences and CD variation in one specific direction was observed.
- CD along the other direction is relatively stable.



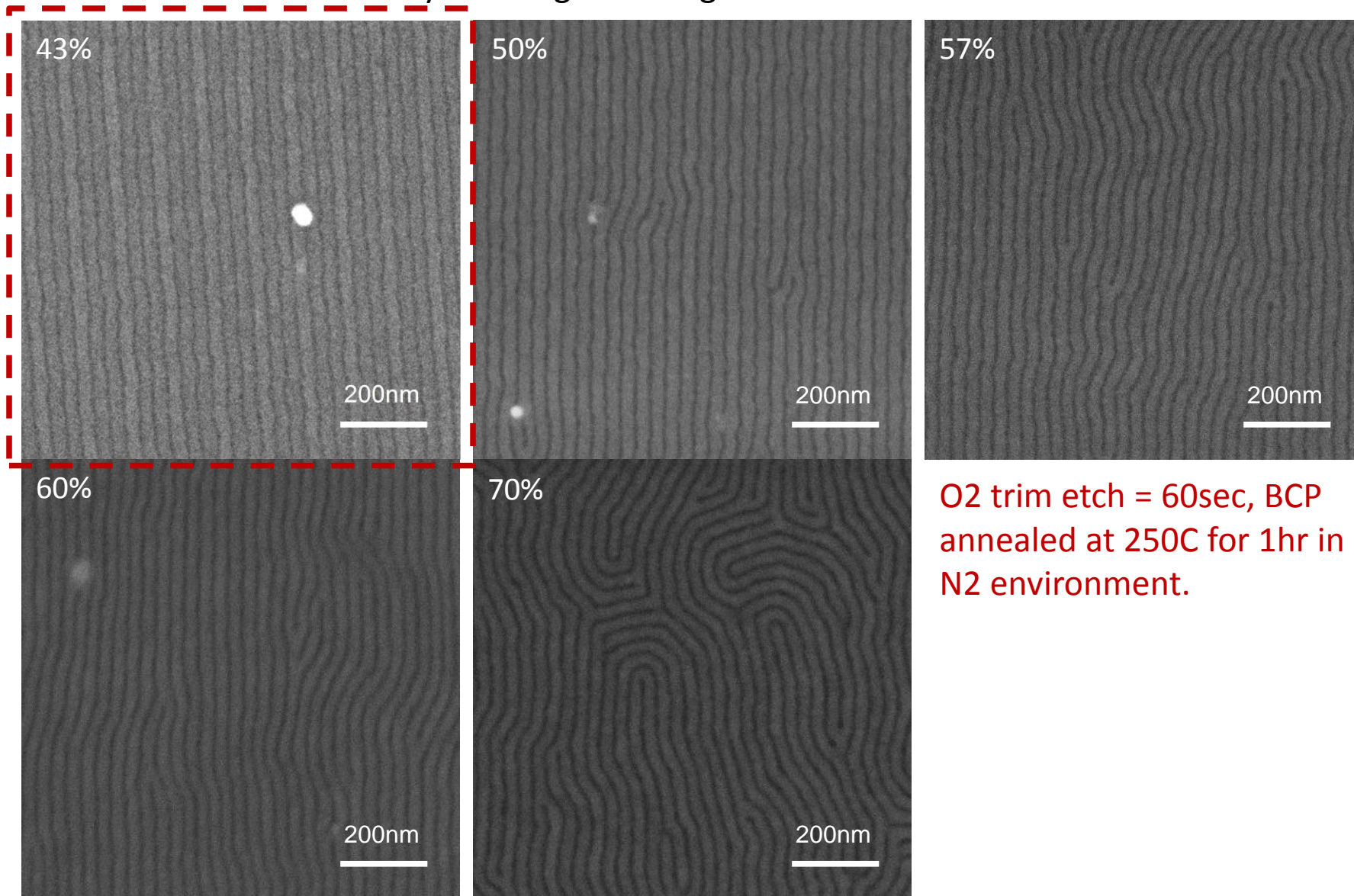
# O<sub>2</sub> trim etch for PR (and X-PS)



- A trim etch for PR is needed to obtain suitable CD for directed assembly.
- Target CD is about  $1/2 L_0$  of the BCP, which is  $\sim 15\text{nm}$ .

# Background chemistry effect on directed assembly

- Random copolymer brushes with different PS content (shown in the images) are used to control the chemistry at background region.



O<sub>2</sub> trim etch = 60sec, BCP annealed at 250C for 1hr in N<sub>2</sub> environment.

X-PS/43%-OH

Pitch of the final structure =  $L_0=30\text{nm}$

BCP annealed at 250C for 1hr

Film thickness  $\sim 23\text{nm}$ .





# Summary and future plan

## Summary

- A 3X density multiplication with a 30nm-pitch final feature size (derived from 90nm pitch guiding pattern) is demonstrated.
- Quasi-optimized CD and background chemistry could result in a very large area of perfection.
- PMMA block can be selectively removed for subsequent pattern transfer.

## Future plan:

- PMMA removal and pattern transfer.
- Start working on hexagonal array patterns.

**BACKUP**

# Non-optimized background chemistry

- Starting from 70% of PS content in the brush composition, “island-hole” structures (non-flat surface) will form.
- Local, small area of perfect assembly may still be observed.

